SPICE Device Model SiA106DJ



Vishay Siliconix

N-Channel 60 V (D-S) MOSFET

DESCRIPTION

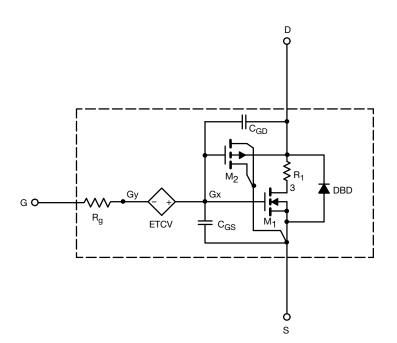
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- · Apply for both linear and switching application
- Accurate over -55 °C to +125 °C temperature range
- Model the gate charge

SUBCIRCUIT MODEL SCHEMATIC



Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits





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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	3	-	V
Drain-source on-state resistance ^a	R _{DS(on)}	V_{GS} = 10 V, I_D = 4 A	0.0145	0.0142	Ω
		$V_{GS} = 7.5 \text{ V}, \text{ I}_{D} = 4 \text{ A}$	0.0172	0.0166	
Forward transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	20	25	S
Diode forward voltage	V _{SD}	I _S = 4 A	0.82	0.85	V
Dynamic ^b					
Input capacitance	C _{iss}	V_{DS} = 30 V, V_{GS} = 0 V, f = 1 MHz	591	540	pF
Output capacitance	C _{oss}		164	150	
Reverse transfer capacitance	C _{rss}		14	11	
Total gate charge	Qg	$V_{DS}=30~V,~V_{GS}=10~V,~I_{D}=4~A$	8.7	8.9	nC
		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 7.5 \text{ V}, \text{ I}_{D} = 4 \text{ A}$	6.5	6.9	
Gate-source charge	Q _{gs}		2.5	2.5	
Gate-drain charge	Q _{gd}		1.8	1.8	

Notes

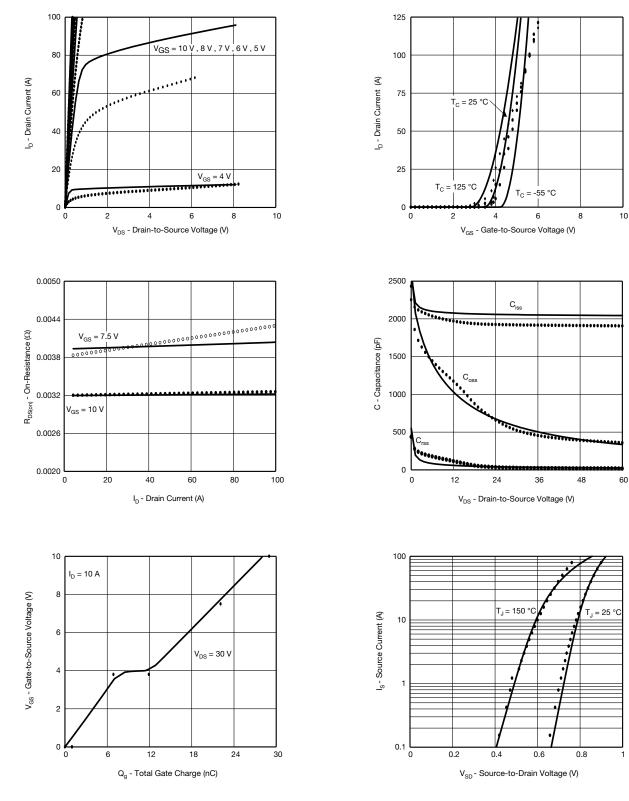
a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%$

b. Guaranteed by design, not subject to production testing



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COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)



Note

Dots and squares represent measured data
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